# Transistors

# General purpose (dual digital transistors) UMD2N / IMD2A

#### Features

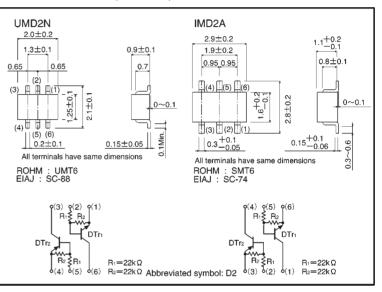
- Both the DTA124E chip and DTC124E chip in a UMT or SMT package.
- Mounting possible with UMT3 or SMT3 automatic mounting machines.
- 3) Transistor elements are independent, eliminating interference.
- Mounting cost and area can be cut in half.

#### Structure

Epitaxial planar type NPN/PNP silicon transistor (Built-in resistor type)

The following characteristics apply to both the DTn<sub>1</sub> and DTn<sub>2</sub>, however, the "–" sign on DTn<sub>2</sub> values for the PNP type have been omitted.

### External dimensions (Units: mm)



#### • Absolute maximum ratings (Ta = $25^{\circ}$ C)

Parameter		Symbol	Limits	Unit	
Supply voltage		Vcc	50	V	
Input voltage		Vin	40	V	
		VIN	-10	V	
Output current		lo	30	mA	
		IC (Max.)	100		
Power dissipation	UMD2N	Pd	150(TOTAL)	*1 mW	
	IMD2A	FU	300(TOTAL)	*2	
Junction temperature		Tj	150	Ĵ	
Storage temperature		Tstg	-55~+150	ĉ	

\*1 120mW per element must not be exceeded.

\*2 200mW per element must not be exceeded.

# •Electrical characteristics (Ta = $25^{\circ}$ C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
	VI (off)	—	_	0.5	v	Vcc=5V, Io=100 μ A	
Input voltage	VI (on)	3	_	—		Vo=0.2V, Io=10mA	
Output voltage	Vo(on)	—	0.1	0.3	V	lo/lı=10mA/0.5mA	
Input current	հ	—	_	0.36	mA	V1=5V	
Output current	IO (off)	_	_	0.5	μA	Vcc=50V, VI=0V	
DC current gain	Gi	56	_	_	—	Vo=5V, Io=5mA	
Transition frequency	fr	—	250	—	MHz	Vce=10mA, Ie=-5mA, f=100MHz *	
Input resistance	R1	15.4	22	28.6	kΩ	_	
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>	0.8	1	1.2	—	_	

\* Transition frequency of the device

#### Packaging specifications

	Packaging type	Taping		
	Code	TR	T108	
Part No.	Basic ordering unit (pieces)	3000	3000	
UMD2N		0	—	
IMD2A			0	

# Electrical characteristic curves DTr1 (NPN)

